

**P-Channel Trench Power MOSFET**
**General Description**

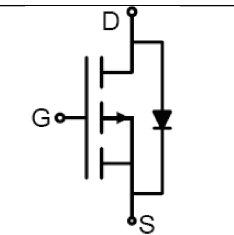
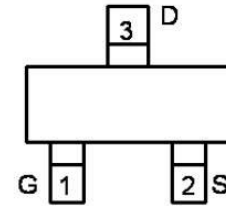
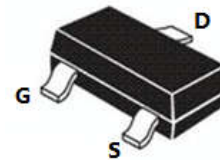
The JY3407AX uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as  $-4.5V$ . This device is suitable for use as a load switch or in PWM applications.

**Features**

- $V_{DS} = -30V, I_D = -4.3A$   
 $R_{DS(ON)} < 50m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = -4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

**Application**

- PWM applications
- Load switch
- Power management


**Schematic Diagram**

**Marking and pin Assignment**

**SOT23 top view**
**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407 or JY3407	JY3407AX	SOT23	Ø180mm	8mm	3000 units

**Table 1. Absolute Maximum Ratings ( $T_A=25^\circ C$ )**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-Source Voltage ( $V_{GS}=0V$ )	-30	V
$V_{GS}$	Gate-Source Voltage ( $V_{DS}=0V$ )	$\pm 20$	V
$I_D$	Drain Current-Continuous	-4.3	A
$I_{DM (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	-30	A
$P_D$	Maximum Power Dissipation	1.5	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

**Table 2. Thermal Characteristic**

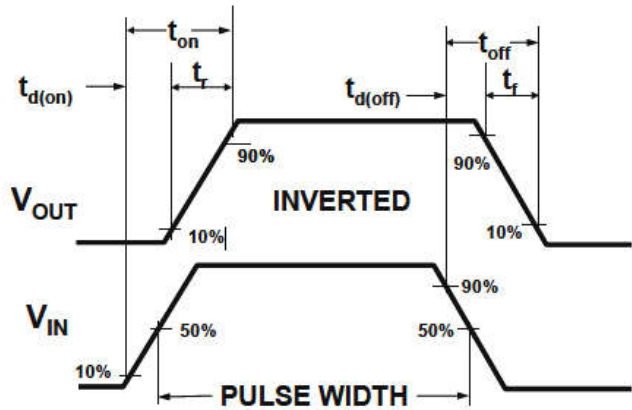
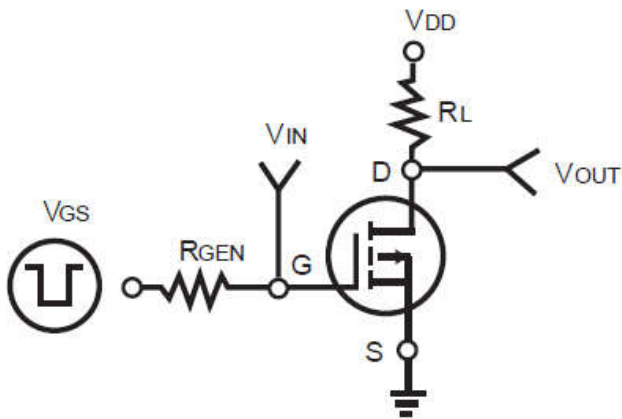
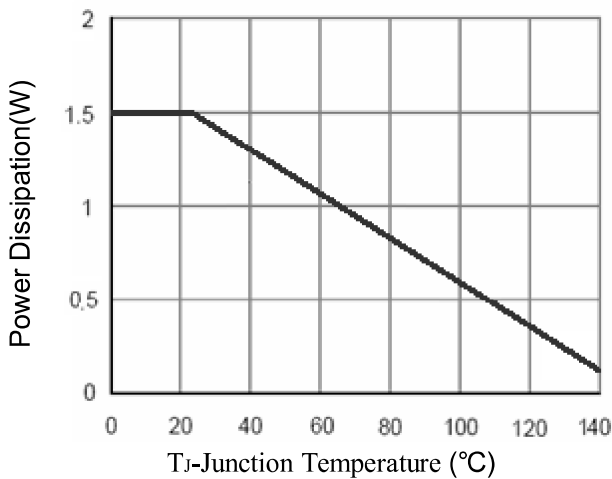
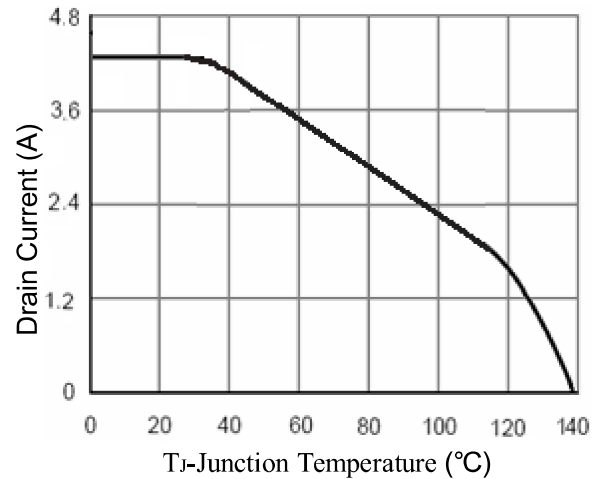
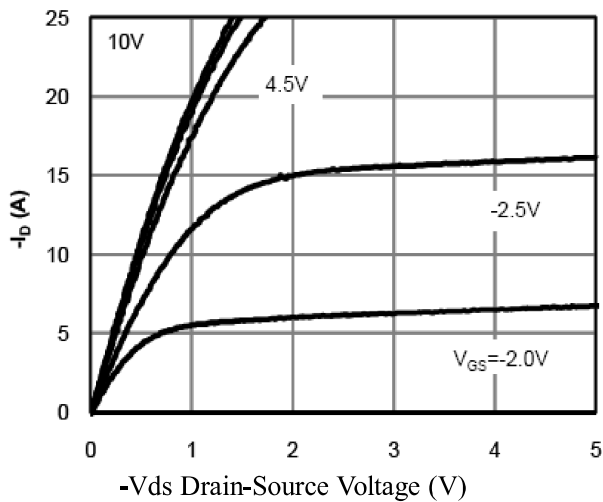
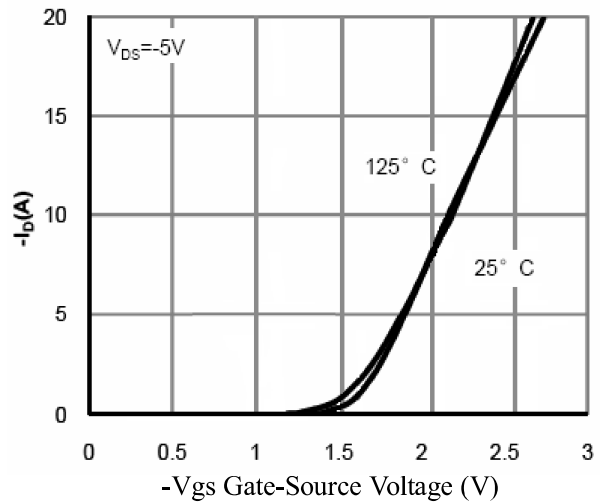
Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	85	$^\circ C/W$



**Table 3. Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
B <sub>VDS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30	-34		V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.6	-2.4	V
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4.3A	4			S
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.3A		38	50	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A		60	100	mΩ
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHz		580		pF
C <sub>oss</sub>	Output Capacitance			98		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			74		pF
<b>Switching Times</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A, R <sub>L</sub> =15Ω V <sub>GS</sub> =-10V, R <sub>G</sub> =2.5Ω		5		nS
t <sub>r</sub>	Turn-on Rise Time			6		nS
t <sub>d(off)</sub>	Turn-Off Delay Time			28		nS
t <sub>f</sub>	Turn-Off Fall Time			7		nS
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.3A, V <sub>GS</sub> =-10V		10		nC
Q <sub>gs</sub>	Gate-Source Charge			2		nC
Q <sub>gd</sub>	Gate-Drain Charge			3		nC
<b>Source-Drain Diode Characteristics</b>						
I <sub>SD</sub>	Source-Drain Current(Body Diode)				-4.3	A
V <sub>SD</sub>	Forward on Voltage <sup>(Note 1)</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A		-0.82	-1	V

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**Switch Time Test Circuit and Switching Waveforms:**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)**
**Figure1. Power Dissipation**

**Figure2. Drain Current**

**Figure3. Output Characteristics**

**Figure4. Transfer Characteristics**


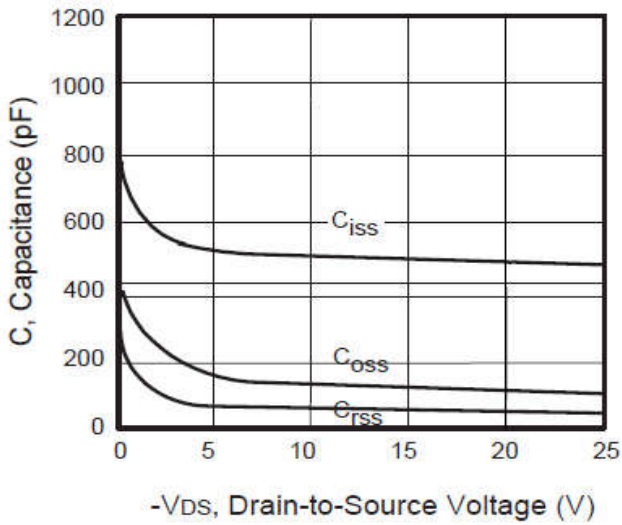
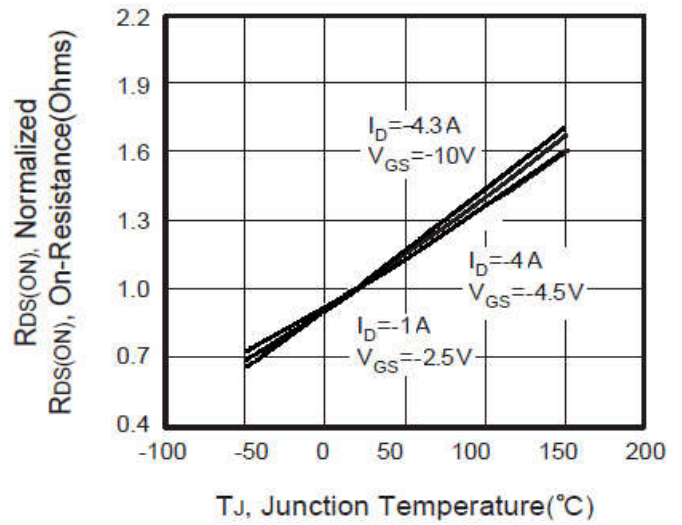
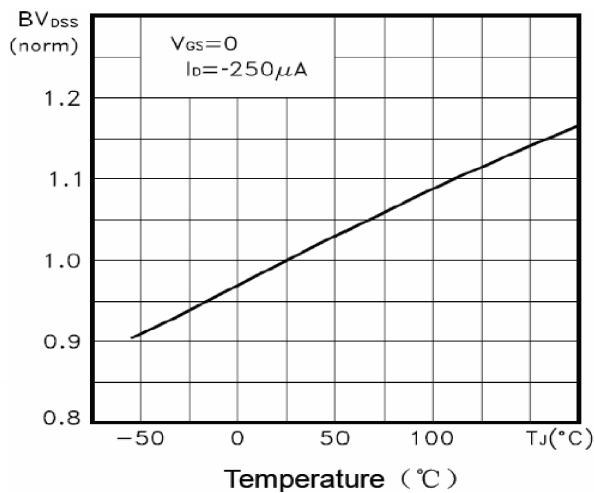
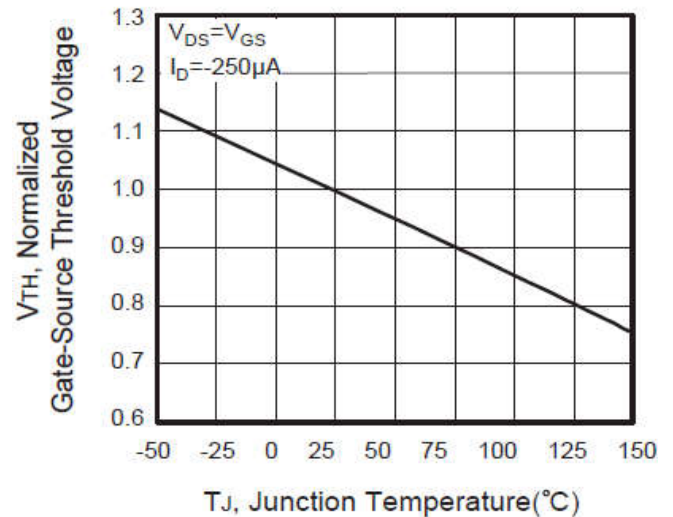
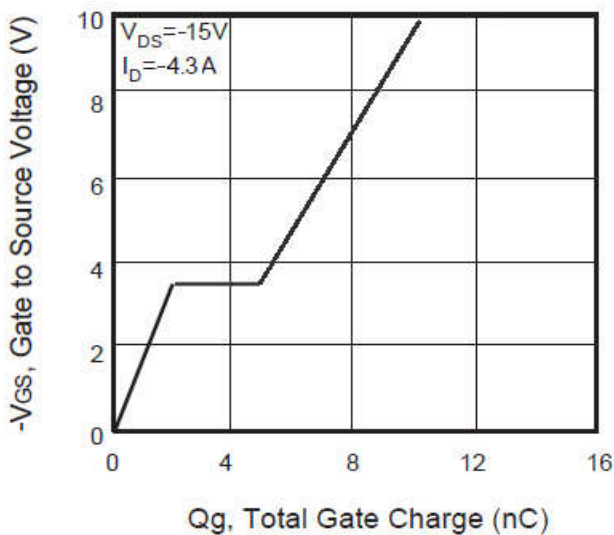
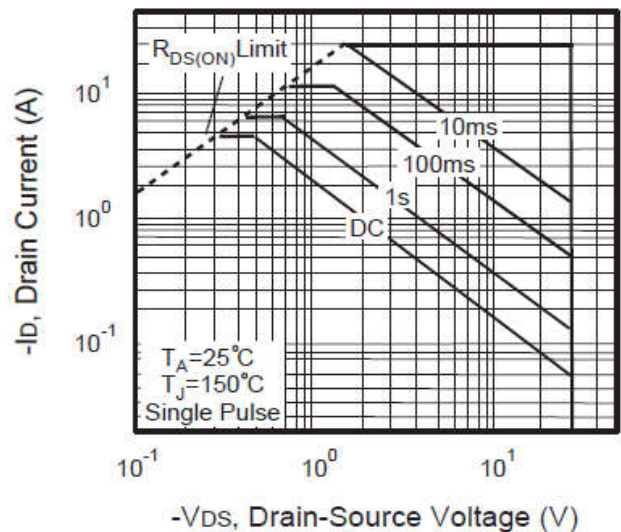
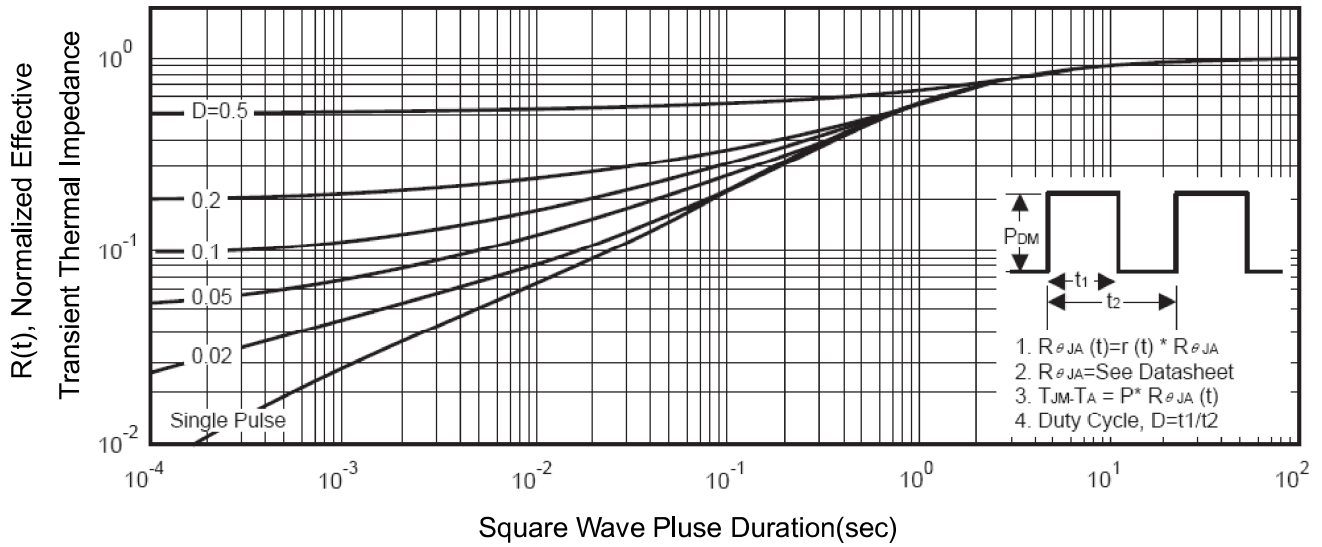
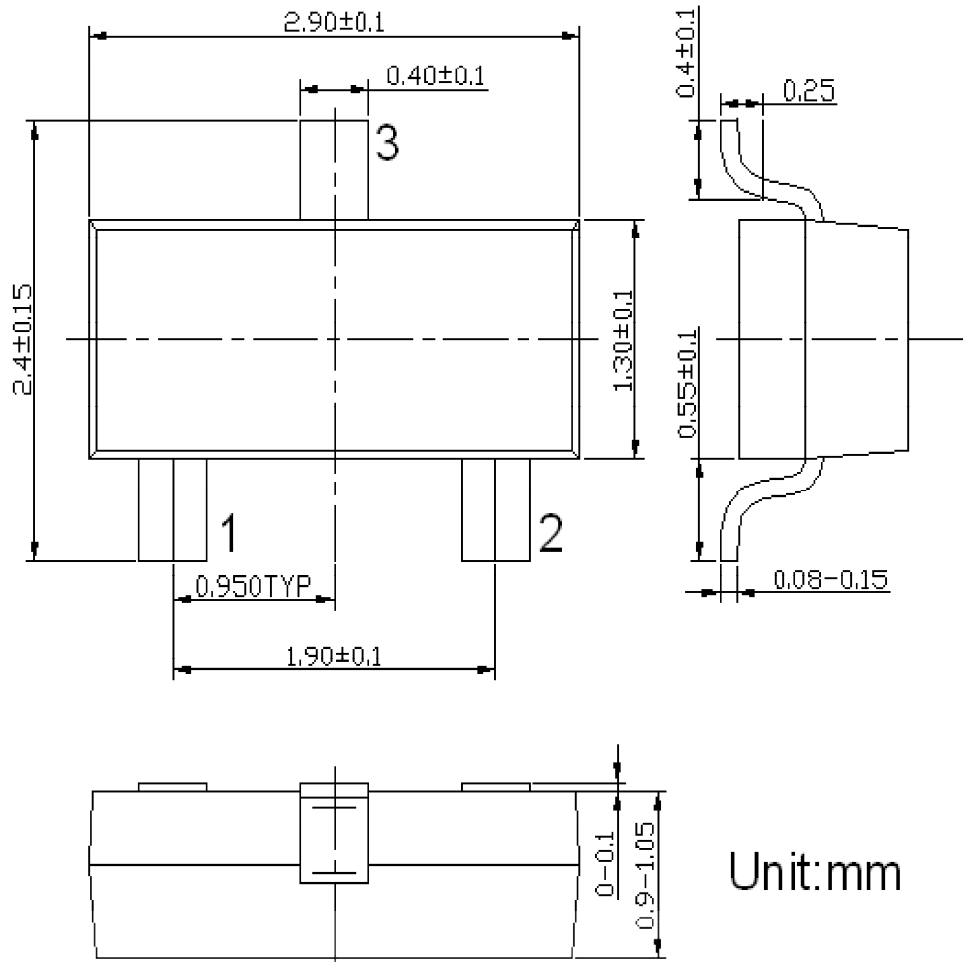
**Figure5. Capacitance**

**Figure6.  $R_{DS(ON)}$  vs Junction Temperature**

**Figure7. Max  $BV_{DSS}$  vs Junction Temperature**

**Figure8.  $V_{GS(th)}$  vs Junction Temperature**

**Figure9. Gate Charge Waveforms**

**Figure10. Maximum Safe Operating Area**




Figure11. Normalized Maximum Transient Thermal Impedance



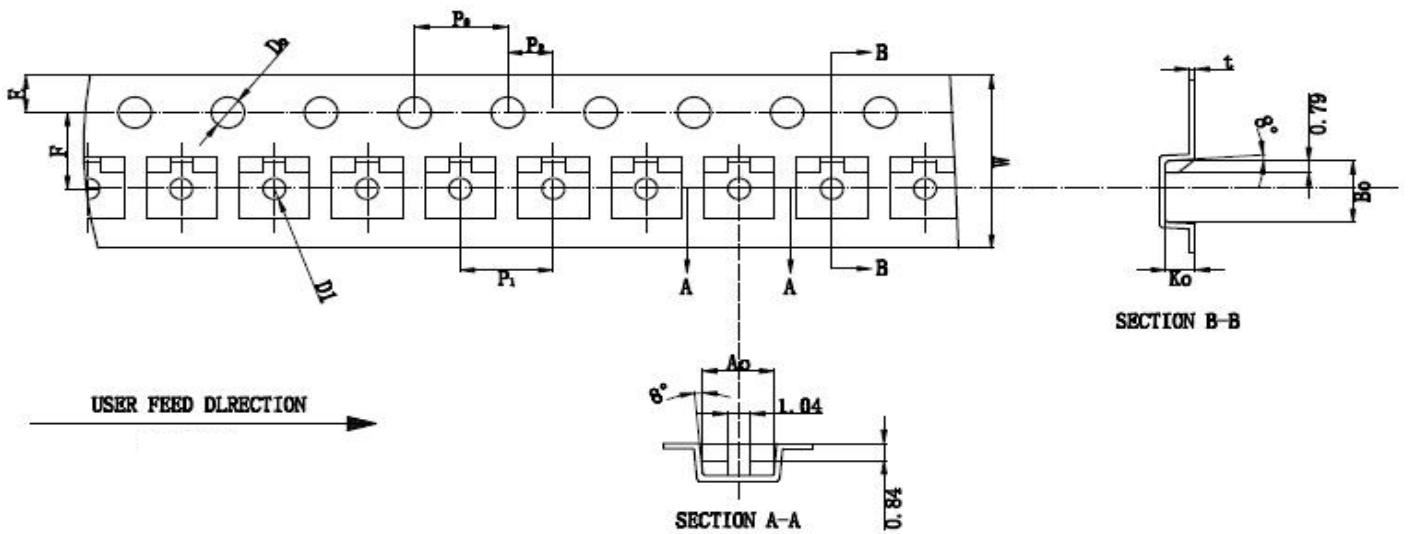
### SOT23 Package Information



**Carrier Dimensions**

PKG TYPE	W	P	E	F	D	D1	Po	Po10	P2
SOT23	8.00	4.00	1.75	3.50	1.50	1.00	4.00	40.00	2.00
Tolerance	+0.3/-0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.2	±0.05

A0	B0	K0	T
3.15	2.77	1.22	0.20
±0.1	±0.1	±0.1	±0.02



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